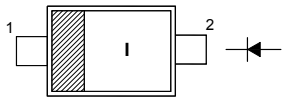
1N6263WT

SILICON SCHOTTKY BARRIER DIODE

for general purpose applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**I**"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit
Peak Repetitive Reverse Voltage		V_{RRM}	60	V
Reverse Voltage		V_R	60	V
Forward Continuous Current		I_{FM}	15	mA
Power Dissipation		P_d	200	mW
Non-Repetitive Peak Forward Surge Current	at t = 1 s at t = 10 µs	I_{FSM}	50 2	mA A
Operating and Storage Temperature Range		T_j, T_{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at I_R = 10 µA	$V_{(BR)R}$	60	-	V
Forward Voltage at I_F = 1 mA at I_F = 15 mA	V_F	- -	0.41 1	V
Reverse Current at V_R = 50 V	I_R	-	200	nA
Total Capacitance at V_R = 0 V, f = 1 MHz	C_T	-	2	pF
Reverse Recovery Time at I_F = I_R = 5 mA , I_{rr} = 0.1X I_R, R_L = 100 Ω	t_{rr}	-	1	ns

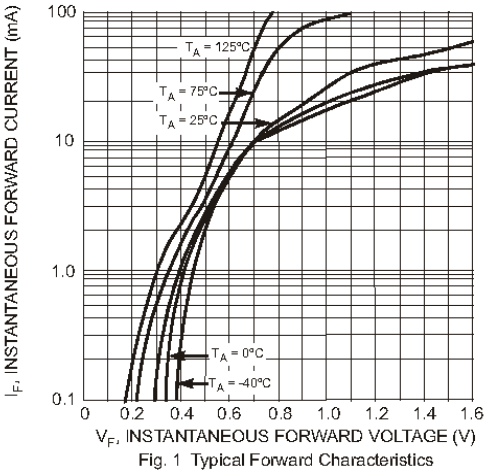


Fig. 1 Typical Forward Characteristics

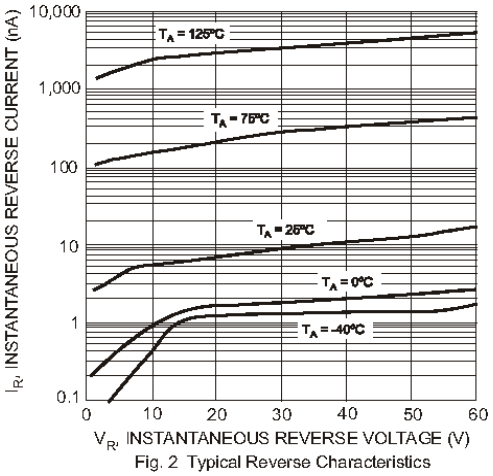


Fig. 2 Typical Reverse Characteristics

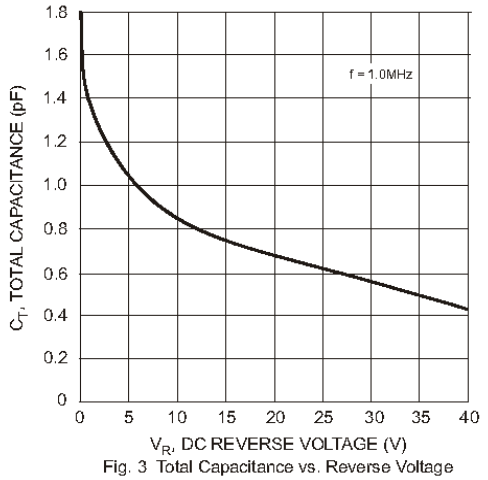


Fig. 3 Total Capacitance vs. Reverse Voltage

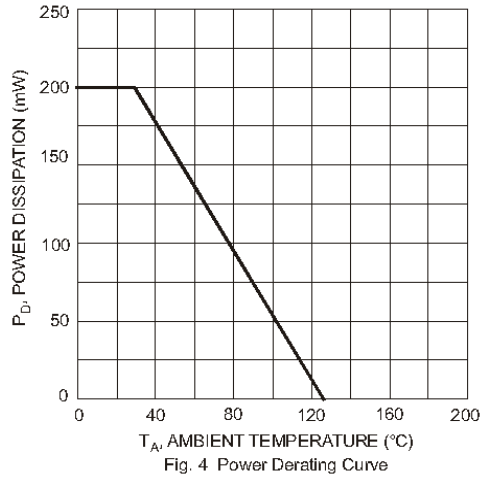
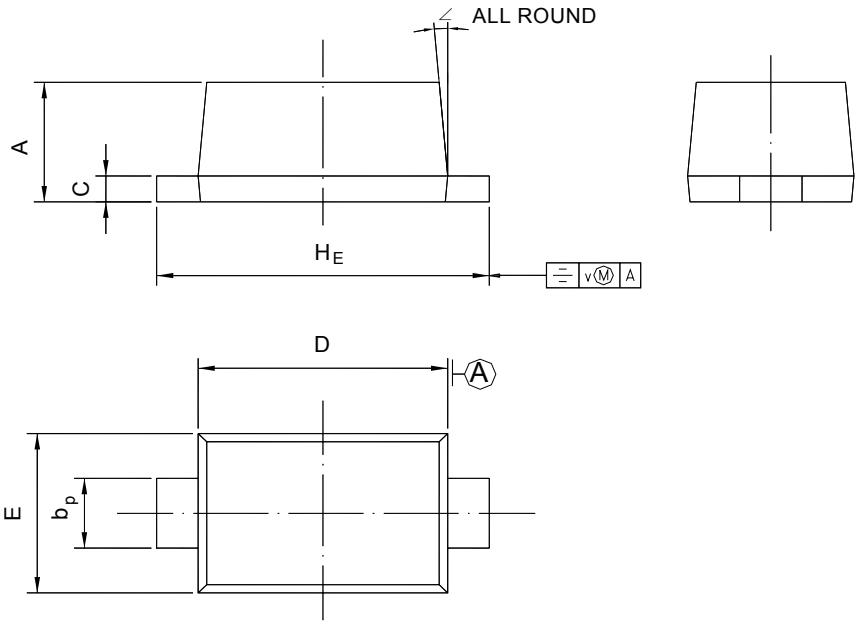


Fig. 4 Power Derating Curve

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°